

# Red Emitting Phosphors $K_2Ge_4O_9:Mn^{4+}$ and $Rb_2Ge_4O_9:Mn^{4+}$

Florian Baur and Thomas Jüstel

Department of Chemical Engineering, Münster University of Applied Sciences, Stegerwaldstr. 39, D-48565 Steinfurt, Germany  
florian.baur@fh-muenster.de, tj@fh-muenster.de

21<sup>st</sup> DAfP-Symposium 2016, June 16-17, Würzburg, Germany

F. Baur, T. Jüstel, J Lumin 177 (2016) 354–360

## Background

- Luminous efficacy and CRI of  $Mn^{4+}$  comprising warm white pcLEDs are strongly influenced by choice of host:

450 nm LED + YAG:Ce +  $Mn^{4+}$  activated phosphor

$K_2SiF_6:Mn^{4+}$  → 337 lm/W,  $R_a = 93$  Peak emission @ 620 nm  
 $Mg_{14}Ge_5O_{24}:Mn^{4+}$  → 241 lm/W,  $R_a = 78$  Peak emission @ 660 nm  
*J. Mater. Chem. C 3 (2015) 2054–2064*

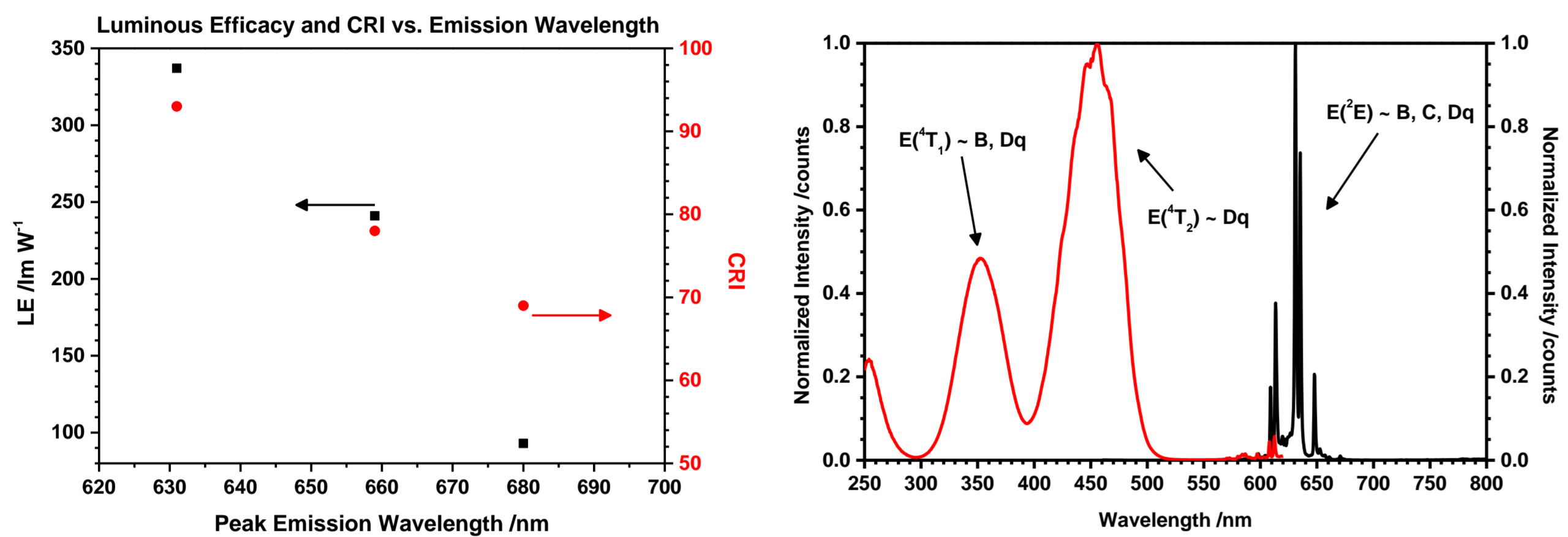


Fig. 1: LE and CRI of warm-white pcLEDs comprising various  $Mn^{4+}$  activated phosphors

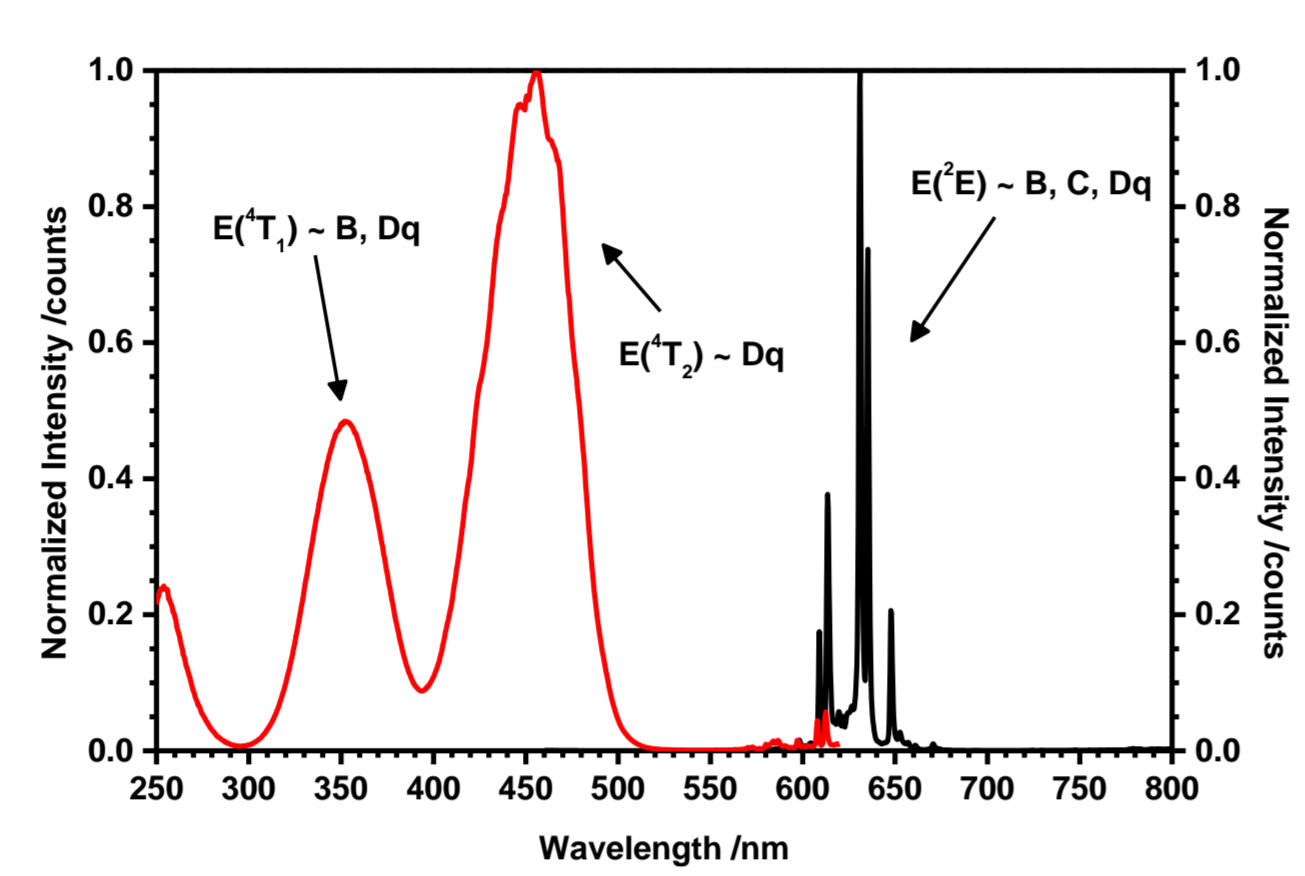


Fig. 2: Influence of Racah parameters B and C and crystal field parameter Dq on  $Mn^{4+}$  properties

## Synthesis and Structure

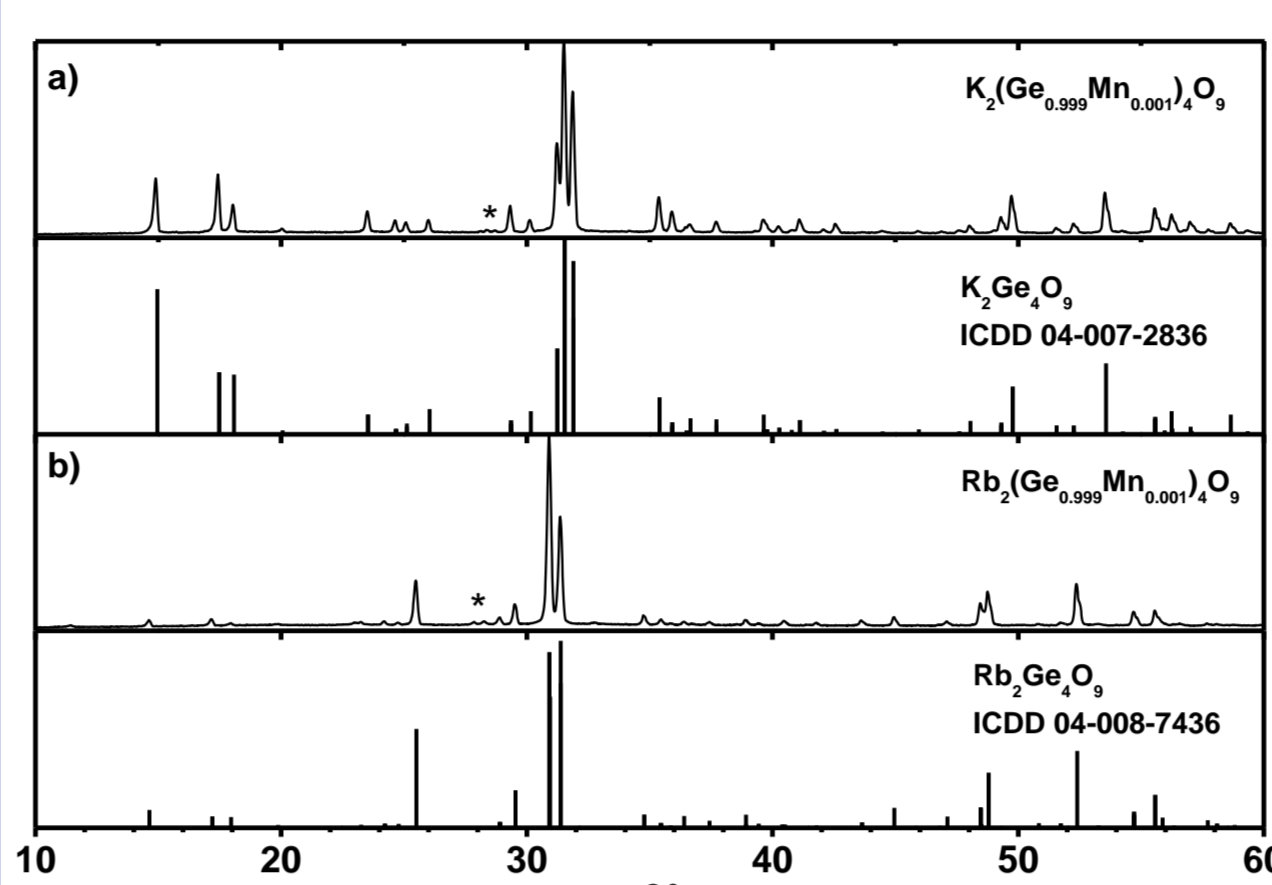


Fig. 3: XRD patterns of a)  $K_2(Ge_{0.999}Mn_{0.001})_4O_9$  and b)  $Rb_2(Ge_{0.999}Mn_{0.001})_4O_9$  for Cu  $K\alpha$  radiation

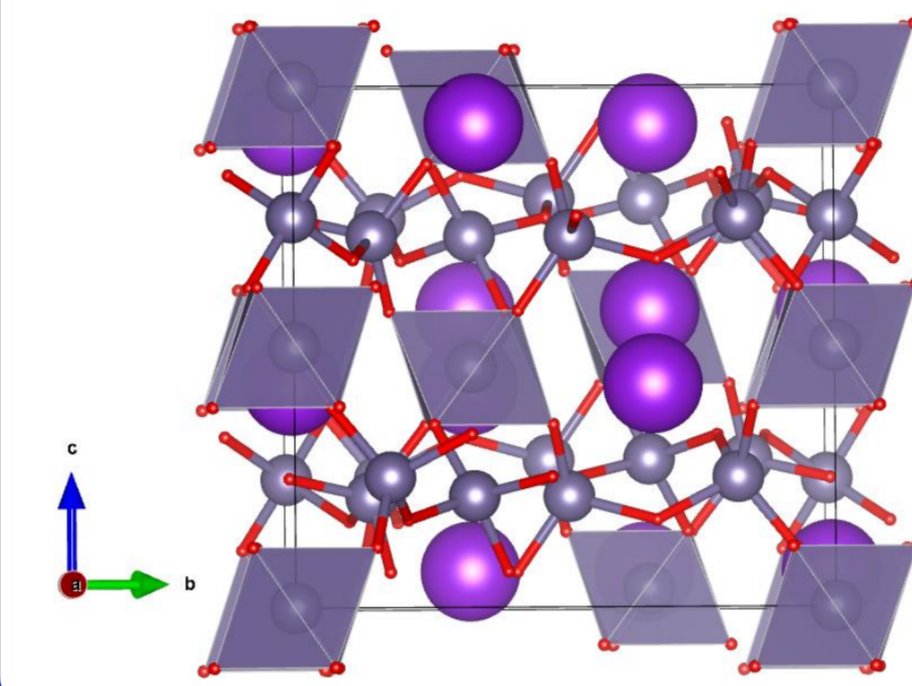


Table 1: Structural data after Redhammer, Tippelt, Acta Cryst C69 (2013) 995

	$K_2Ge_4O_9$	$Rb_2Ge_4O_9$
a/nm	1.18461	1.21008
b/nm	0.98009	0.98722
Ge1 octahedron		
<Ge-O> /pm	190.8	190.7
Angle axial-axial	180.00°	180.00°
Site symmetry	3	3
Ge4 octahedron		
<Ge-O3>	188.6	189.1
<Ge-O4>	186.5	187.0
Angle axial-axial	178.18°	178.58°
Site symmetry	3	3

- $K_2Ge_4O_9$  and  $Rb_2Ge_4O_9$  are isostructural
- $Ge_3O_9$  rings form layers connected by  $GeO_6$  octahedra
- Two crystallographically distinct  $GeO_6$  octahedra:
  - Ge(1) exhibits inversion symmetry
  - Ge(4) does not exhibit inversion symmetry

## Results and Discussion

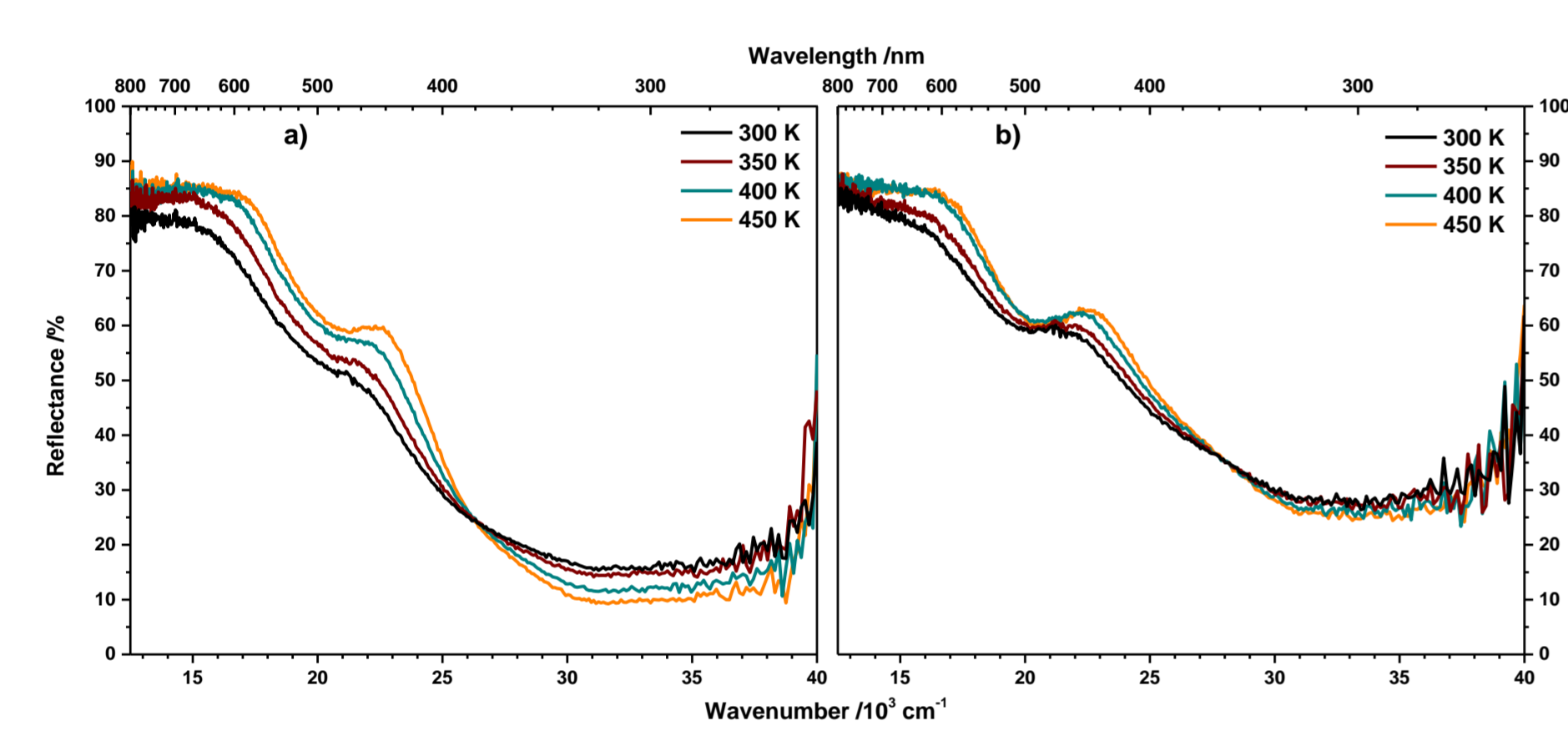


Fig. 4: Reflection spectra of a)  $K_2(Ge_{0.999}Mn_{0.001})_4O_9$  and b)  $Rb_2(Ge_{0.999}Mn_{0.001})_4O_9$  recorded at various temperatures.

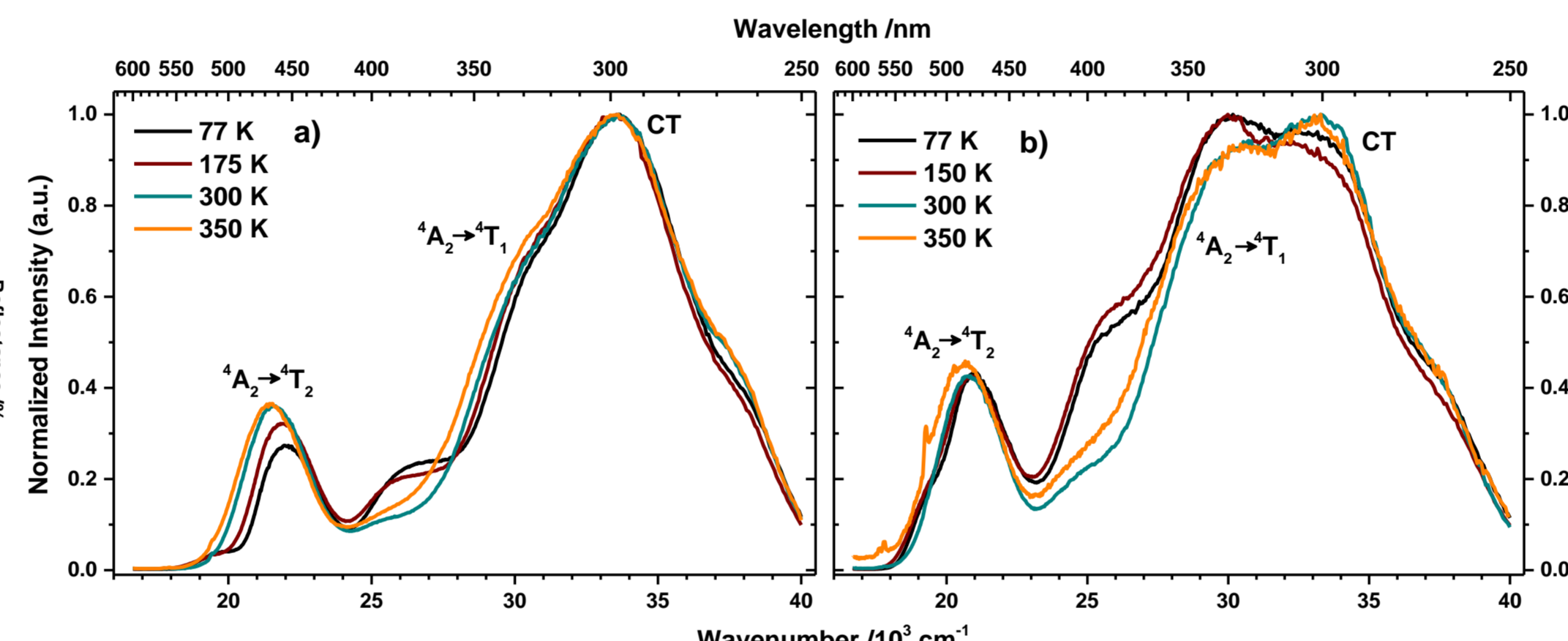


Fig. 5: Excitation spectra of a)  $K_2(Ge_{0.999}Mn_{0.001})_4O_9$  and b)  $Rb_2(Ge_{0.999}Mn_{0.001})_4O_9$  recorded at various temperatures.

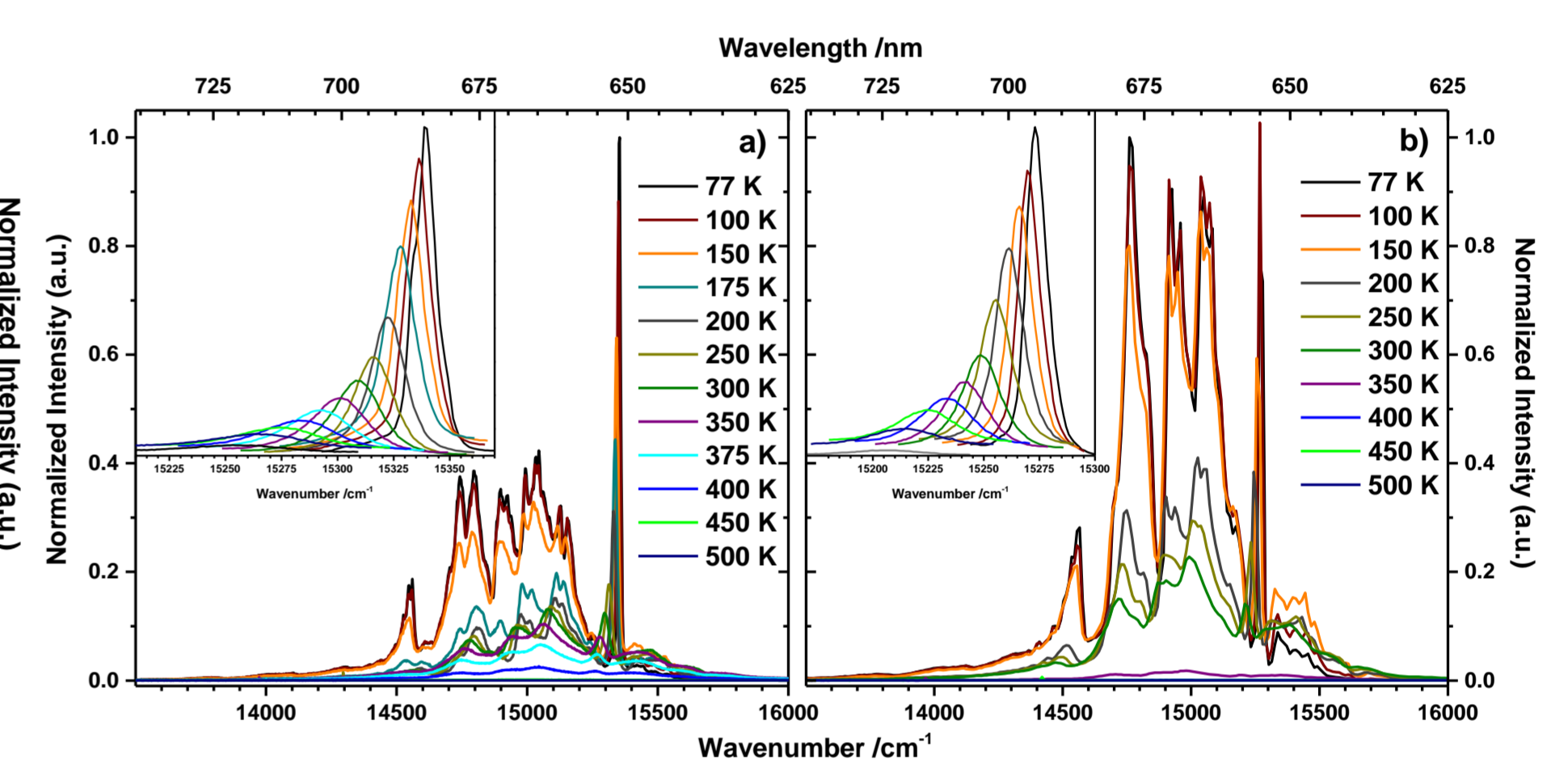


Fig. 6: Emission spectra of a)  $K_2(Ge_{0.999}Mn_{0.001})_4O_9$  and b)  $Rb_2(Ge_{0.999}Mn_{0.001})_4O_9$  recorded at various temperatures.

- Significant changes of the optical properties can be observed with increasing temperature:
- $^4A_2 \rightarrow ^4T_2$  transition red-shifts from 453 nm (22072  $cm^{-1}$ ) to 467 nm (21395  $cm^{-1}$ )
- Distance between  $^4T_2$  and  $^4T_1$  peak increases
- $^2E \rightarrow ^4A_2$  transition ZPL blue-shifts from 652.0 nm (15339  $cm^{-1}$ ) to 655.5 nm (15256  $cm^{-1}$ )
- Crystal field splitting increases with increasing temperature
- Racah parameter B increases with increasing temperature
- Racah parameter C decreases with increasing temperature
- Increase of Dq and B can be explained by thermal expansion of the host material
- Decrease of C is unexpected!

Phosphor	B / $cm^{-1}$	C / $cm^{-1}$	M-O-Mn angle
$CaZrO_3:Mn^{4+}$	650	3173	146.50 °
$SrTiO_3:Mn^{4+}$	719	2812	180.00 °
$GdAlO_3:Mn^{4+}$	600	~ 3200	156.65 °
$LaAlO_3:Mn^{4+}$	700	~ 2900	171.90 °

- Racah parameter C can apparently be linked to M-O-Mn bond angle
  - Bond angles close to 180 ° result in low value of C
  - Racah parameter B and C do not necessarily follow the same trend
  - Small Mn-O distance results in a lower thermal quenching temperature

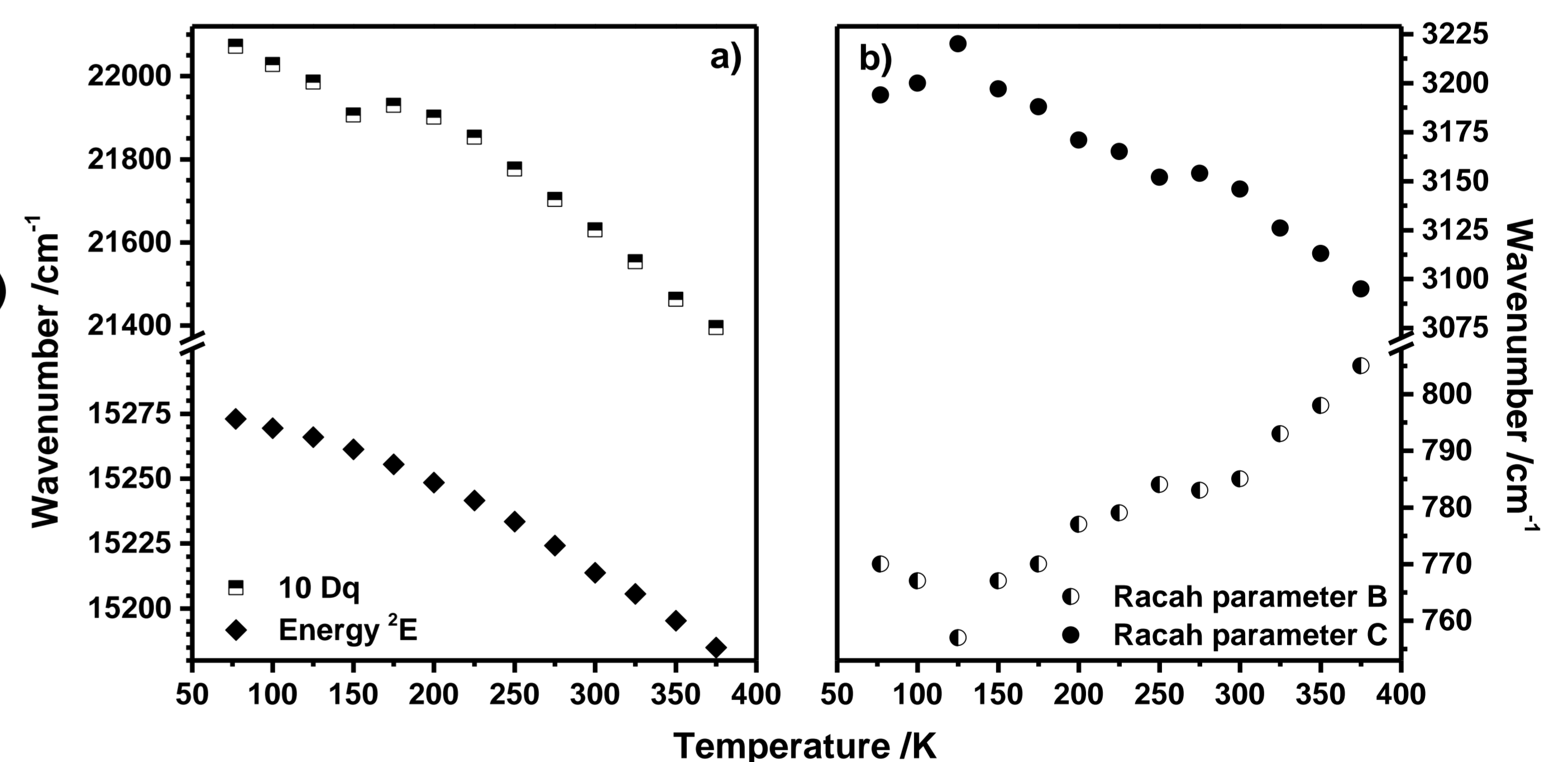


Fig. 7: a) Crystal field parameter Dq and energy of  $^2E$  and b) Racah parameters B and C of  $K_2(Ge_{0.999}Mn_{0.001})_4O_9$  depending on temperature.

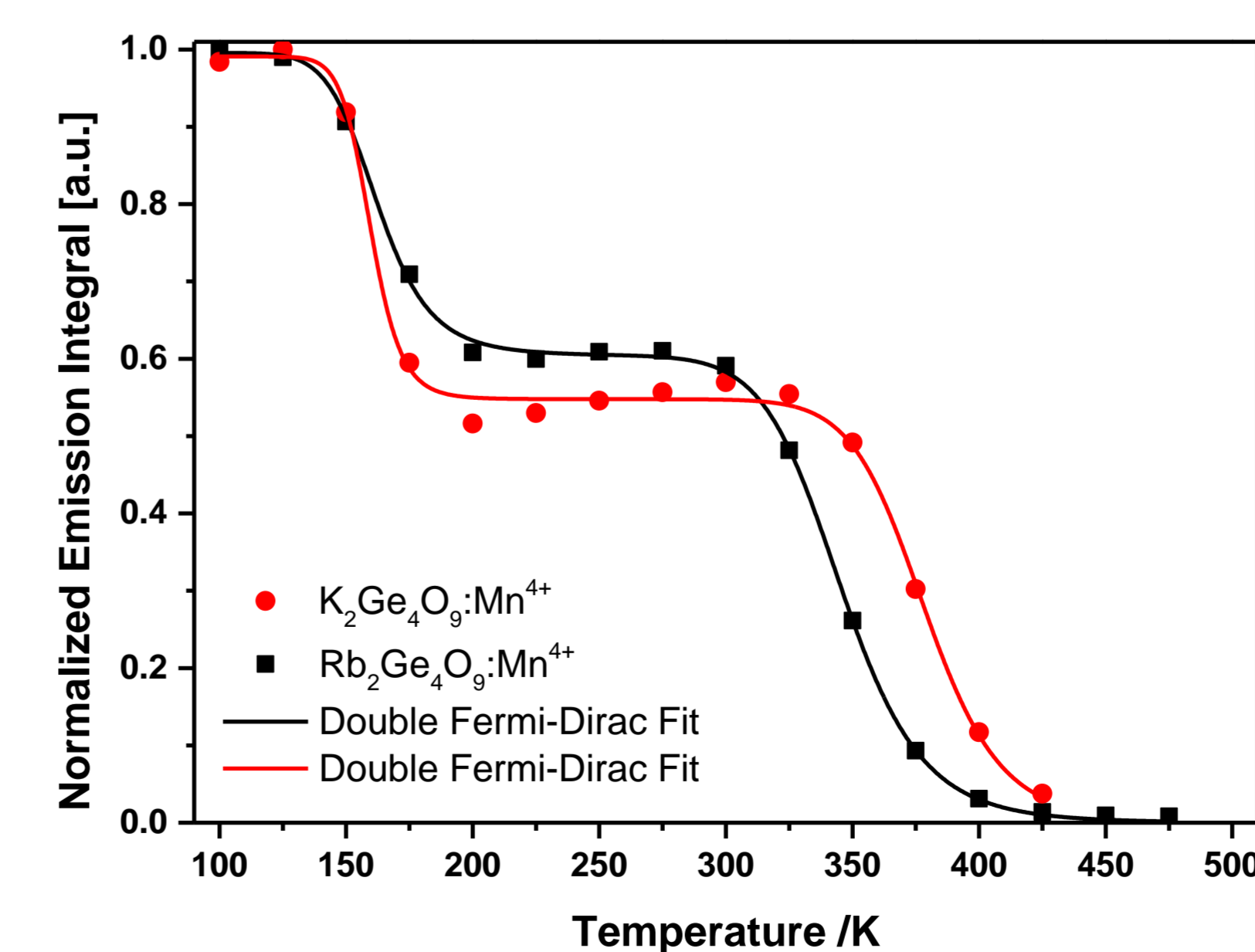


Fig. 8: Thermal quenching curves of (red)  $K_2Ge_4O_9:Mn^{4+}$  (black)  $Rb_2Ge_4O_9:Mn^{4+}$ .

- Bi-sigmoidal TQ-curves were observed
  - Thermal quenching curves show strong correlation of  $T_{1/2}$  to the Mn-O distance
- |                      |                       |
|----------------------|-----------------------|
| $K_2Ge_4O_9:Mn^{4+}$ | $Rb_2Ge_4O_9:Mn^{4+}$ |
| $T_{1/2,a} = 160$ K  | $T_{1/2,a} = 162$ K   |
| $T_{1/2,b} = 379$ K  | $T_{1/2,b} = 346$ K   |
- Compare to Table 1!

